CLAIMS

1. A sputtering target for a magnetic recording medium, comprising: a metal phase containing Pt and at least one or more selected from Mn and V, with the balance being Co and incidental impurities; and an oxide phase which contains ~~containing~~ at least B and O and does not contain Mg and Al.

2. The sputtering target for a magnetic recording medium according to Claim 1, containing, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt and 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V; and

comprising, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.

3. A sputtering target for a magnetic recording medium, comprising: a metal phase containing Pt, at least one or more selected from Mn and V, and ~~at least one or more selected from Cr and~~ Ru, with the balance being Co and incidental impurities; and an oxide phase which ~~containing~~ contains at least B and O and does not contain Mg and Al.

4. The sputtering target for a magnetic recording medium according to Claim 3, containing, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt, 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V, and more than 0.5 mol% and 30 mol% or less of ~~at least one or more selected from Cr and~~ Ru; and

comprising, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.

5. The sputtering target for a magnetic recording medium according to any one of Claims 1 to 4, wherein the oxide phase further contains an oxide of at least one element selected from V, Ru, Ti, Si, Ta, Cr, ~~Al,~~ Nb, Mn, Co, Ni, Zn, Y, Mo, W, La, Ce, Nd, Sm, Eu, Gd, Yb, Lu, and Zr.

6. A sputtering target for a magnetic recording medium, comprising: a metal phase

containing Pt and at least one or more selected from Mn and V, with the balance being Co and incidental impurities; and an oxide phase which does not contain Mg and Al.

7. The sputtering target for a magnetic recording medium according to Claim 6, containing, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt and 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V; and

comprising, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.

8. A sputtering target for a magnetic recording medium, comprising: a metal phase containing Pt, at least one or more selected from Mn and V, and ~~at least one or more selected from Cr and~~ Ru, with the balance being Co and incidental impurities; and an oxide phase which does not contain Mg and Al.

9. The sputtering target for a magnetic recording medium according to Claim 8~~7~~,

containing, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt, 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V, and more than 0.5 mol% and 30 mol% or less of ~~at least one or more selected from Cr and~~ Ru; and

comprising, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.

10. The sputtering target for a magnetic recording medium according to any one of Claims 6 to 9, wherein the oxide phase further contains an oxide of at least one element selected from B, V, Ru, Ti, Si, Ta, Cr, ~~Al,~~ Nb, Mn, Co, Ni, Zn, Y, Mo, W, La, Ce, Nd, Sm, Eu, Gd, Yb, Lu, and Zr.